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| How much ECC do I have to example to put downes? I am using the correct amount of error correction code (ECC) for the NAND device, but i'm still seeing bit/byte errors in data i took back from the NAND device. How do I achieve greater PROGRAM/READ throughput for the NAND device? How do I achieve greater PROGRAM/READ throughput for the NAND device? How do I achieve greater PROGRAM/READ throughput for the NAND device? How do I achieve greater PROGRAM/READ throughput for the NAND device? How do I achieve greater PROGRAM/READ throughput for the NAND device? How do I achieve greater PROGRAM/READ throughput for the NAND device? How do I achieve greater provide the to many errors to beet from is this true? Should I be marking blacks had due to READ arrors? When Listne a Read ID command (001) to a two-site NAND device. I get a device ID tack that states it is a ene-die NAND device. Where can I find auditional information about Micron NAND devices that is not covered in the device data pheete? Why was lighting a bit/byte error reading back the information i programmed into the NAND device? Why doesn't the NAND Flash device respond correctly to commande issued to R? Boos thermal information change for IT patts? Wy device many reading and the VDOQ (1-50). But now we've discovered that JTAG is actually publicly to VDOQ (1-50). But may and the take the specification is still to VDOQ + 0.0V + 1.8V, but with CMOS parts there's no way I cen guarance that it won't can be considered to the specification is still to VDOQ + 0.0V + 1.8V, but with CMOS parts there's no way I cen guarance that it won't can be prediction? What is a base to be a specification at the specification base of the driver in taking significant bisit is to be applied by a specification at the specification at the specification is still to VDOQ + 0.0V + 1.8V, but with CMOS parts there's no way I cen guarance th | 2. | | | | |
| How do Lachieve greater PROGRAM/READ throughput for the NAND device? How is Nvb specified? Lam seeing a lot of READ DISTURB errors. Can you tell me if there is a problem with your part? Lew heard that NAND has too many errors to boot from te this inte? Should Lbe marking blocks bed due to READ error? When I issue a Read ID commend (ROh) to a two-die NAND device, I get a device ID back that states it is a one-die NAND device. Where can I find additional technical information about Micron NAND devices that is not covered in the device data sheets? Where can I find additional technical information about Micron NAND devices that is not covered in the device data sheets? Why doesn't the NAND Flash device respond correctly to commands issued to it? Does thermal information change for IT parts? My design was based on a specification stating the JTAG was relative to VDD (1 SV), but now we've discovered that JTAG is actually relative to VDD (1 SV). It's a fairly significant board spin to change this, what do I risk by leaving the design asis? I assume that the specification is still for VDIG > 0.3Y = 1 8V, but with CMOS parts there's no way i can guarantee that it won't explication? What is a "bank"? What is a "bank"? What is a "bank"? What is a "bank"? | Ŧ | | | | |
| Does thermal information change for IT parts? My design was based on a specification stating the JTAG was relative to VDD (1.8V), but now we've discovered that JTAG is actually relative to VDDQ (1.5V). It's a fairly significant board spin to change this; what do I risk by leaving the design as-is? I assume that the specification is still for VDDQ + 0.3V = 1.8V, but with CMOS parts there's no way I can guarantee that it won't swing past that on transitions. Should the ECC memory chip share chip select and CKE signals with the other two main memory chips in our point-to-point application? What is a "bank"? What is the impedance tolerance of the driver in match-impedance mode relative to the expected value base on the perfect reference resistor connected to ZQ pin? | | | | | |
| Should the ECC memory chip share chip select and CKE signals with the other two main memory chips in our point-to-point application? What is a "bank"? What is the impedance tolerance of the driver in match-impedance mode relative to the expected value base on the perfect reference resistor connected to ZQ pin? | ÷ | | | | |
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